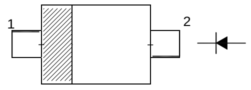
1N5817WB~1N5819WB

1 A Surface Mount Schottky Barrier Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Simplified outline SOD-123 and symbol

* Lead Free Finish/RoHS Compliant

Absolute Maximum Ratings (T_a = 25 °C)

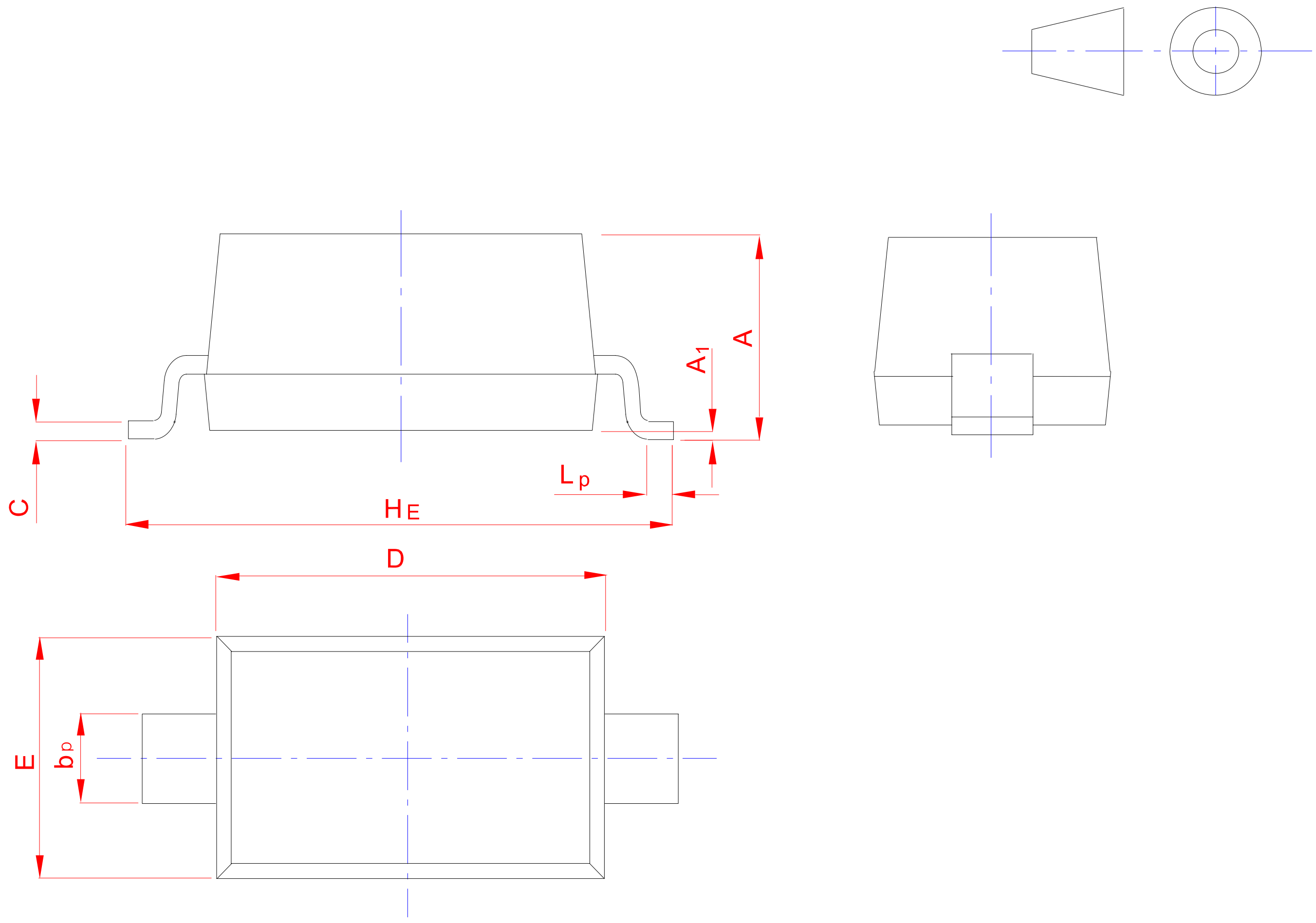
Parameter		Symbol	Value	Unit
Reverse Voltage	1N5817WB	V_R	20	V
	1N5818WB		30	
	1N5819WB		40	
Average Forward Rectified Current		$I_{F(AV)}$	1	A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)		I_{FSM}	9	A
Power Dissipation		P_{tot}	450	mW
Operating Temperature Range		T_j	- 55 to + 125	°C
Storage Temperature Range		T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage		$V_{(BR)R}$			V
at I_R = 1 mA	1N5817WB		20	-	
	1N5818WB		30	-	
	1N5819WB		40	-	
Reverse Current		I_R			mA
at V_R = 20 V	1N5817WB		-	1	
at V_R = 30 V	1N5818WB		-	1	
at V_R = 40 V	1N5819WB		-	1	
at V_R = 4 V	1N5819WB		-	0.05	
at V_R = 6 V	1N5819WB		-	0.075	
Forward Voltage		V_F			V
at I_F = 0.1 A	1N5819WB		-	0.45	
at I_F = 1 A	1N5817WB		-	0.45	
	1N5818WB		-	0.55	
	1N5819WB		-	0.6	
at I_F = 3 A	1N5817WB		-	0.75	
	1N5818WB		-	0.875	
	1N5819WB		-	0.9	
Total Capacitance at V_R = 4 V, f = 1 MHz		C_{tot}	-	120	pF

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-123**



UNIT	A	b_p	C	**D**	E	H_E	A_1	L_p
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20